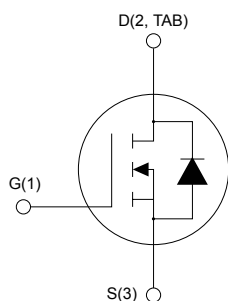
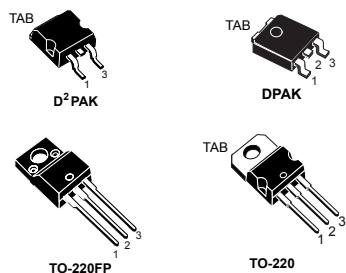




STB11N65M5, STD11N65M5 STF11N65M5, STP11N65M5

Datasheet

N-channel 650 V, 430 mΩ typ., 9 A MDmesh M5 Power MOSFETs in D²PAK, DPAK, TO-220FP and TO-220 packages



AM01475v1_noZen



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STB11N65M5	650 V	480 mΩ	9 A
STD11N65M5			
STF11N65M5			
STP11N65M5			

- 100% avalanche tested
- Excellent switching performance
- Extremely low R_{DS(on)}
- Low gate charge and input capacitance

Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs based on the MDmesh M5 innovative vertical process technology combined with the well-known PowerMESH horizontal layout. The resulting products offer extremely low on-resistance, making them particularly suitable for applications requiring high power and superior efficiency.

Product status links

[STB11N65M5](#)

[STD11N65M5](#)

[STF11N65M5](#)

[STP11N65M5](#)

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D ² PAK DPAK TO-220	TO-220FP	
V _{GS}	Gate-source voltage	±25		V
I _D	Drain current (continuous) at T _C = 25 °C	9	9 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	5.6	5.6 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	36	36 ⁽¹⁾	A
P _{TOT}	Total power dissipation at T _C = 25 °C	85	25	W
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T _C = 25 °C)	-	2.5	kV
T _J	Operating junction temperature range	-55 to 150		°C
T _{stg}	Storage temperature range			

- Limited by maximum junction temperature.
- Pulse width limited by safe operating area.
- $I_{SD} \leq 9\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS}(\text{peak}) < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.

Table 2. Thermal data

Symbol	Parameter	Value				Unit
		D ² PAK	DPAK	TO-220FP	TO-220	
R _{thJC}	Thermal resistance, junction-to-case	1.47		5.0	1.47	°C/W
R _{thJA}	Thermal resistance, junction-to-ambient	30 ⁽¹⁾	50 ⁽¹⁾	62.5		°C/W

- When mounted on a standard 1 inch² area of FR-4 PCB with 2-oz copper.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _J max.)	2	A
E _{AS}	Single pulse avalanche energy (starting T _J = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	130	mJ

2 Electrical characteristics

($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	650	-	-	V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$, $T_C = 125\text{ }^{\circ}\text{C}^{(1)}$	-	-	100	μA
I_{GSS}	Gate body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$	-	-	± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 4.5\text{ A}$	-	430	480	m Ω

1. Specified by design, not tested in production.

Table 5. Dynamic

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	644	-	pF
C_{oss}	Output capacitance			18		pF
C_{rss}	Reverse transfer capacitance			2.5		pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }520\text{ V}$, $V_{GS} = 0\text{ V}$	-	55	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	17	-	pF
R_g	Gate input resistance	$f = 1\text{ MHz}$ open drain	-	5	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 4.5\text{ A}$,	-	17	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 0\text{ to }10\text{ V}$		4.6		nC
Q_{gd}	Gate-drain charge	(see the Figure 19. Test circuit for gate charge behavior)		8.5		nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
$t_{d(v)}$	Voltage delay time	$V_{DD} = 400\text{ V}$, $I_D = 7.5\text{ A}$,	-	23	-	ns
$t_{r(v)}$	Voltage rise time	$R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$		10		ns
$t_{c(off)}$	Crossing time	(see the Figure 20. Test circuit for inductive load switching and diode recovery times and		13		ns
$t_{f(i)}$	Fall time	Figure 23. Switching time waveform)		13.5		ns

Table 7. Source drain diode

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-	-	9	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				36	
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 9\text{ A}$, $V_{GS} = 0\text{ V}$	-	-	1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see the Figure 20. Test circuit for inductive load switching and diode recovery times)	-	232	-	ns
Q_{rr}	Reverse recovery charge			2		μC
I_{RRM}	Reverse recovery current			17.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see the Figure 20. Test circuit for inductive load switching and diode recovery times)	-	328	-	ns
Q_{rr}	Reverse recovery charge			2.8		μC
I_{RRM}	Reverse recovery current			17		A

1. Pulse width limited by safe operating area.

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics curves

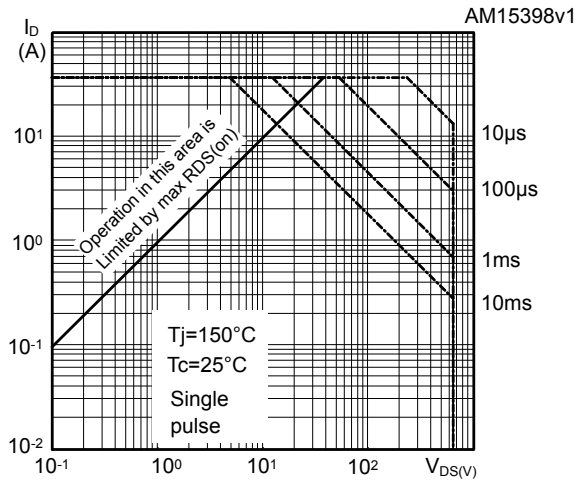
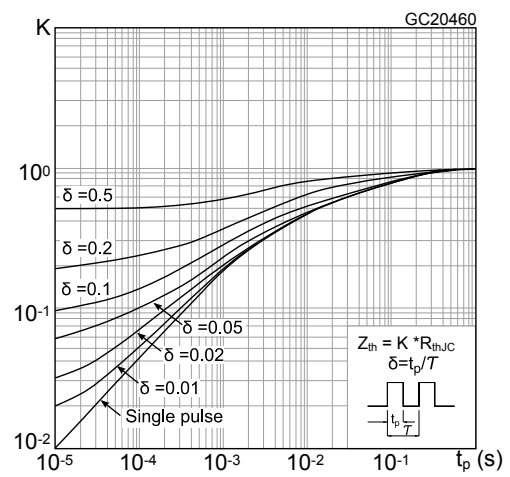
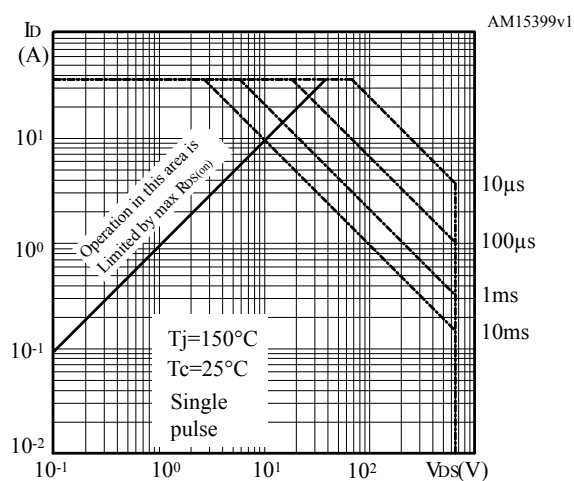
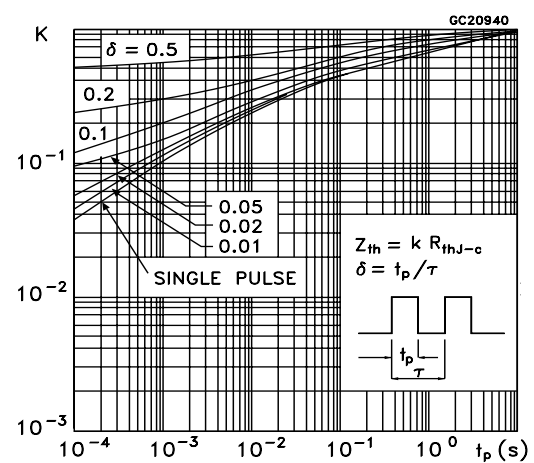
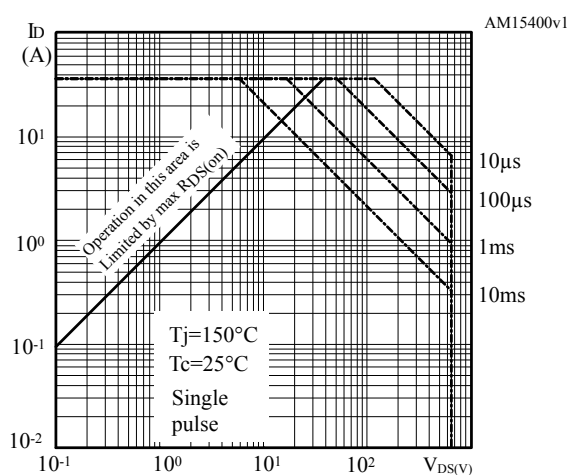
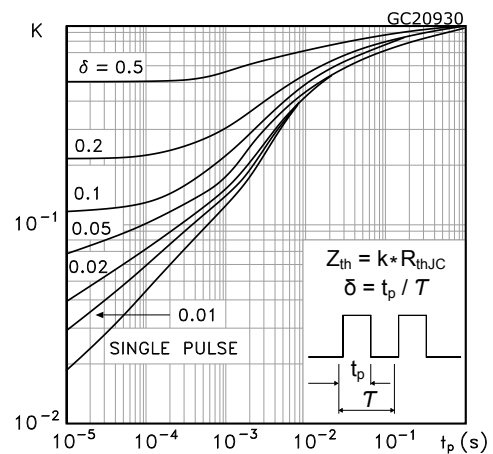
Figure 1. Safe operating area for DPAK

Figure 2. Thermal impedance for DPAK

Figure 3. Safe operating area for TO-220FP

Figure 4. Thermal impedance for TO-220FP

Figure 5. Safe operating area for TO-220 and D²PAK

Figure 6. Thermal impedance for TO-220 and D²PAK


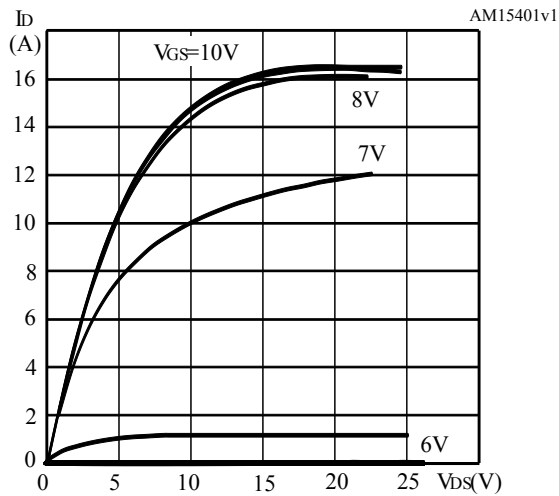
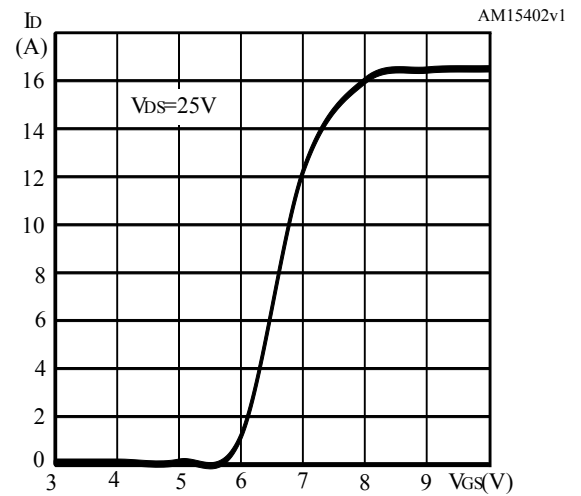
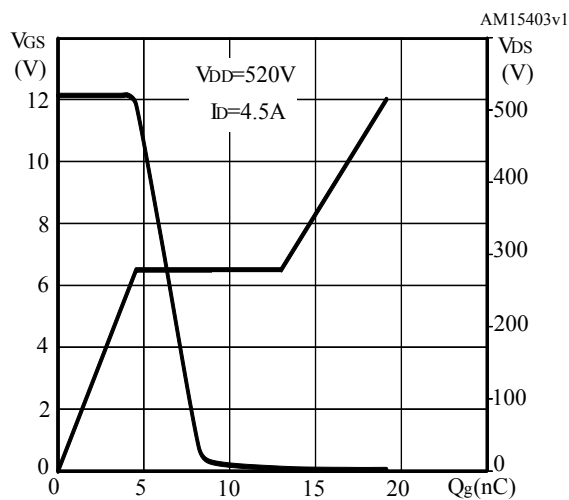
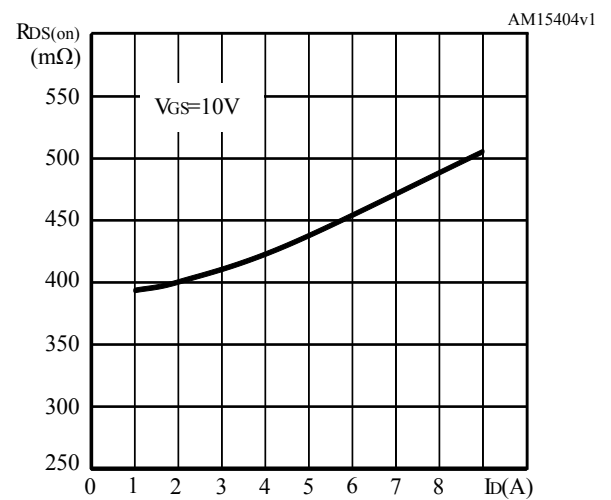
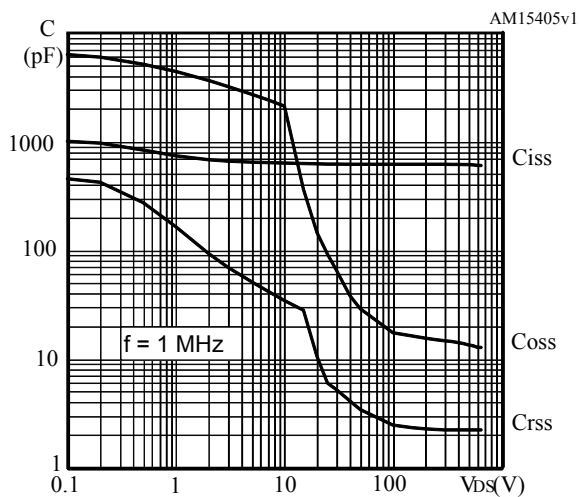
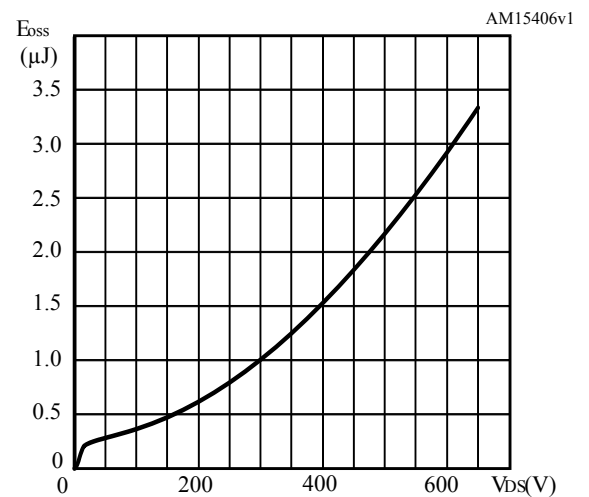
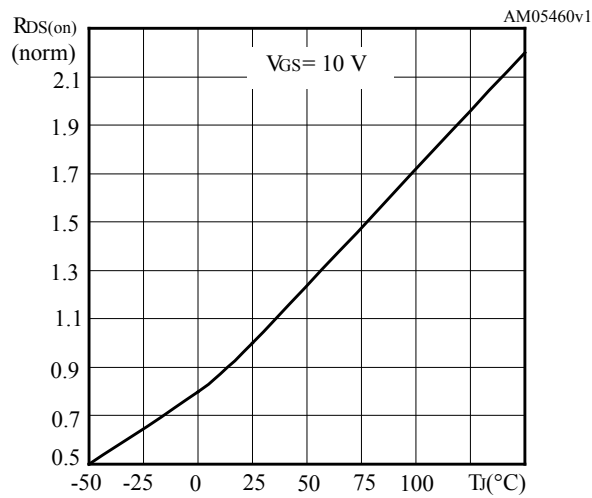
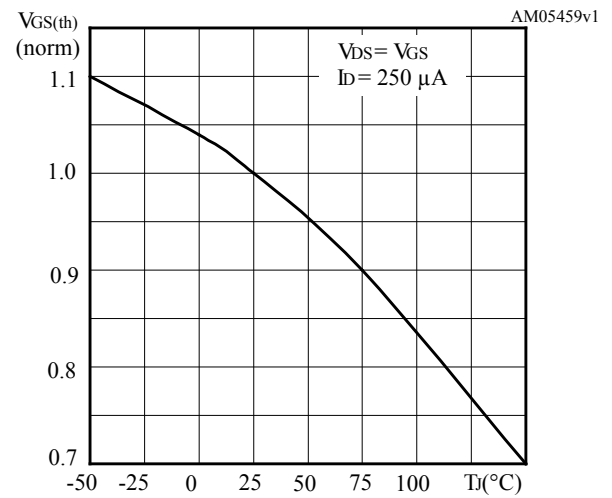
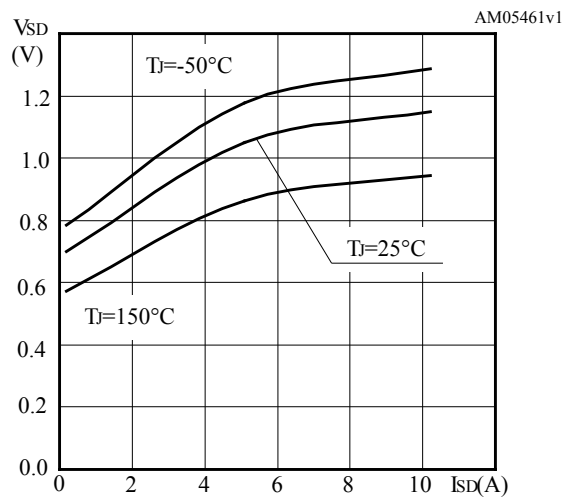
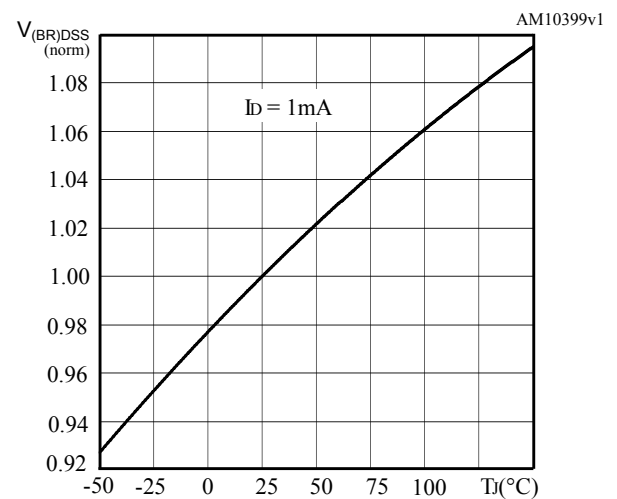
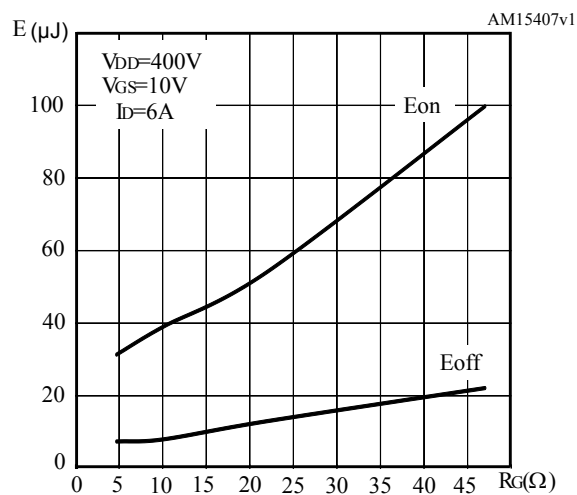
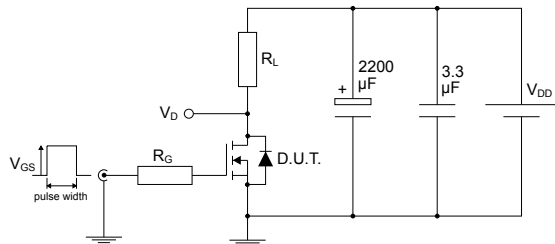
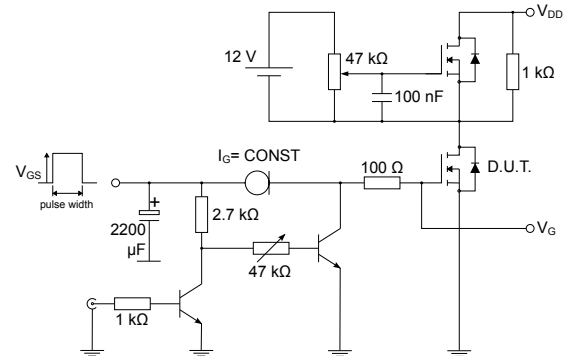
Figure 7. Output characteristics

Figure 8. Transfer characteristics

Figure 9. Gate charge vs gate-source voltage

Figure 10. Static drain-source on resistance

Figure 11. Capacitance variations

Figure 12. Output capacitance stored energy


Figure 13. Normalized on-resistance vs temperature

Figure 14. Normalized gate threshold voltage vs temperature

Figure 15. Drain-source diode forward characteristics

Figure 16. Normalized V(BR)DSS vs temperature

Figure 17. Switching energy vs gate resistance


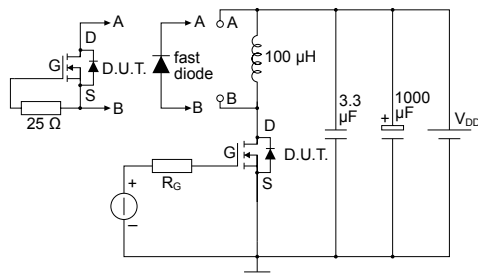
3 Test circuits

Figure 18. Test circuit for resistive load switching times


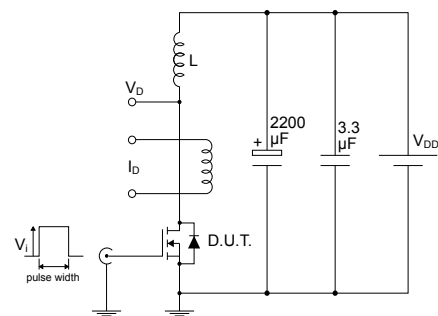
AM01468v1

Figure 19. Test circuit for gate charge behavior


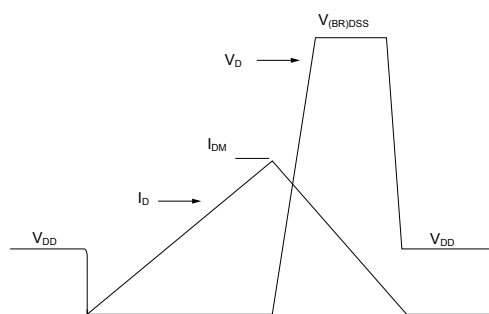
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Figure 20. Test circuit for inductive load switching and diode recovery times


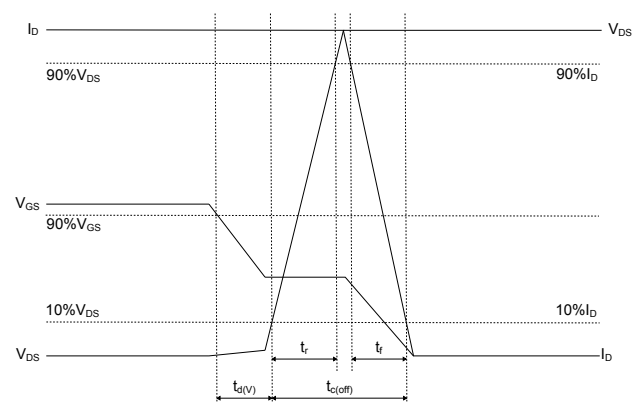
AM01470v1

Figure 21. Unclamped inductive load test circuit


AM01471v1

Figure 22. Unclamped inductive waveform


AM01472v1

Figure 23. Switching time waveform


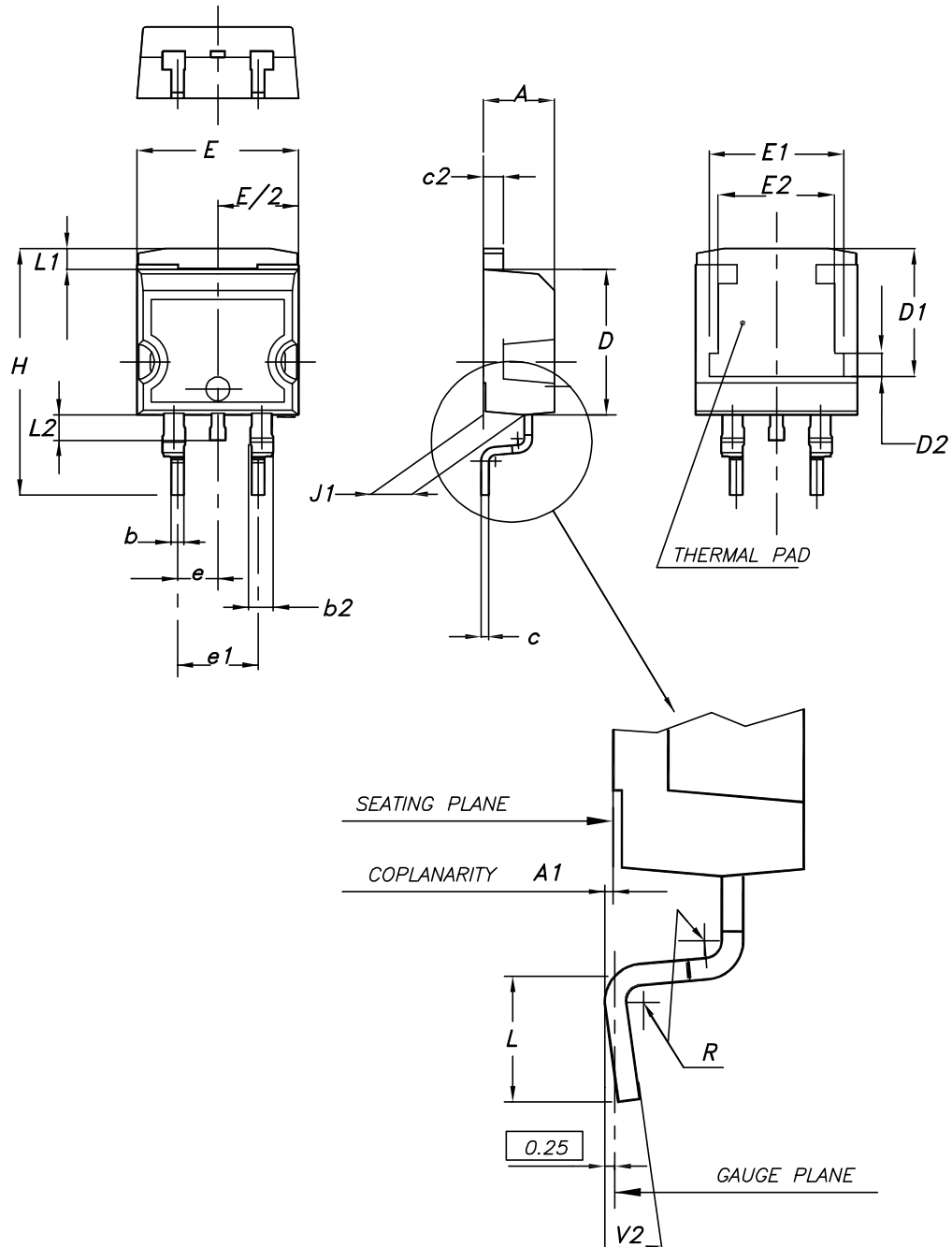
AM05540v2

4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 D²PAK (TO-263) type A package information

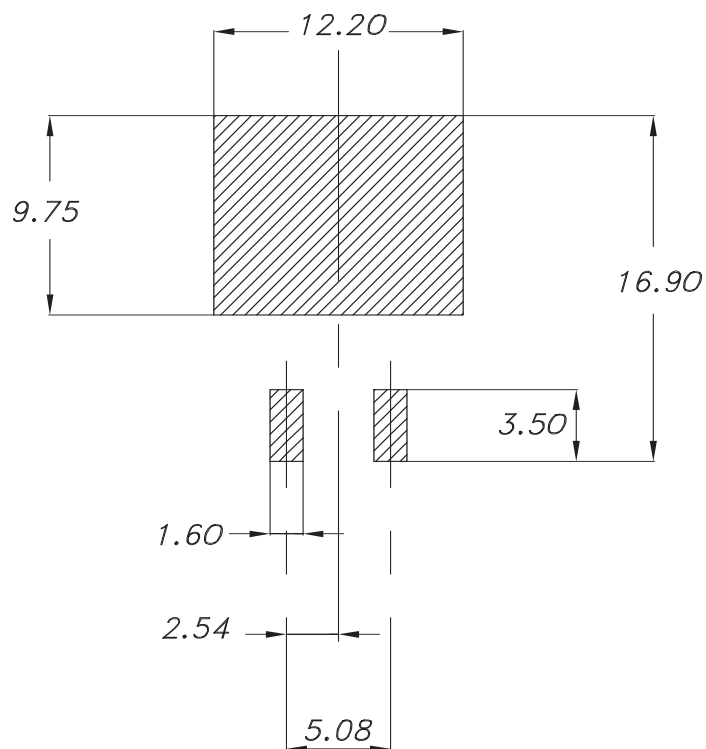
Figure 24. D²PAK (TO-263) type A package outline



0079457_27

Table 8. D²PAK (TO-263) type A package mechanical data

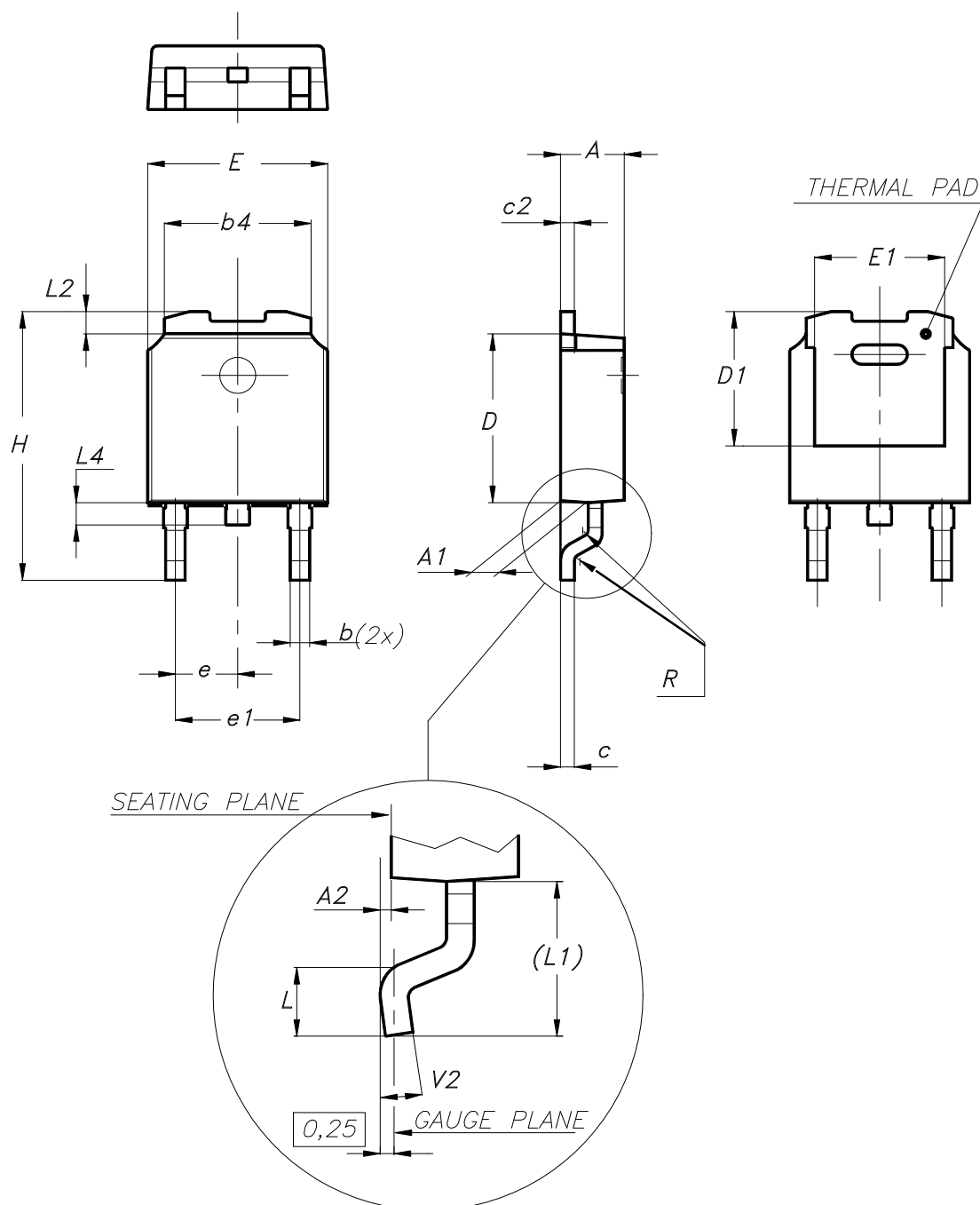
Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.30	8.50	8.70
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

Figure 25. D²PAK (TO-263) recommended footprint (dimensions are in mm)


0079457_Rev27_footprint

4.2 DPAK (TO-252) type A package information

Figure 26. DPAK (TO-252) type A package outline



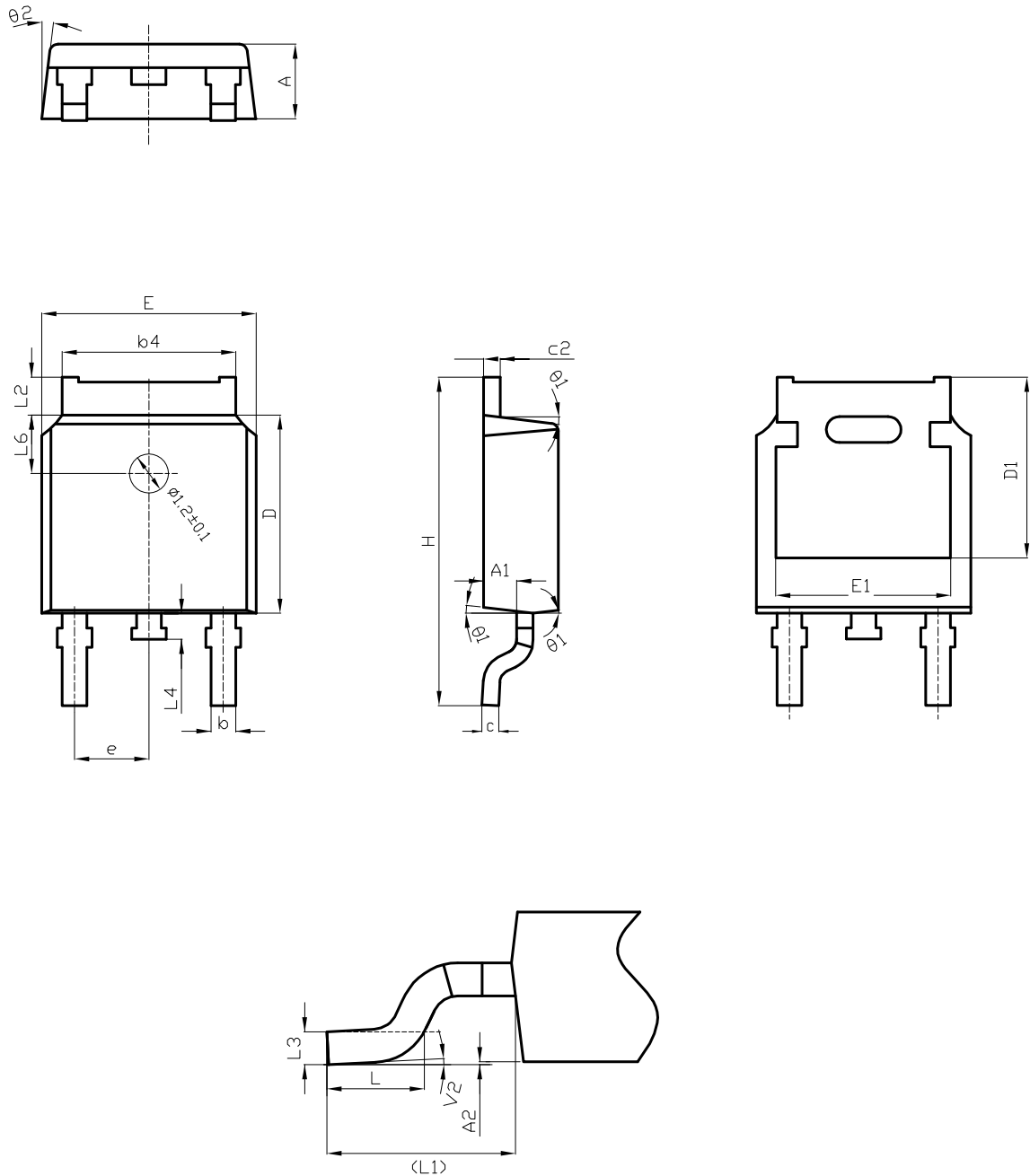
0068772_A_36

Table 9. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.3 DPAK (TO-252) type C2 package information

Figure 27. DPAK (TO-252) type C2 package outline



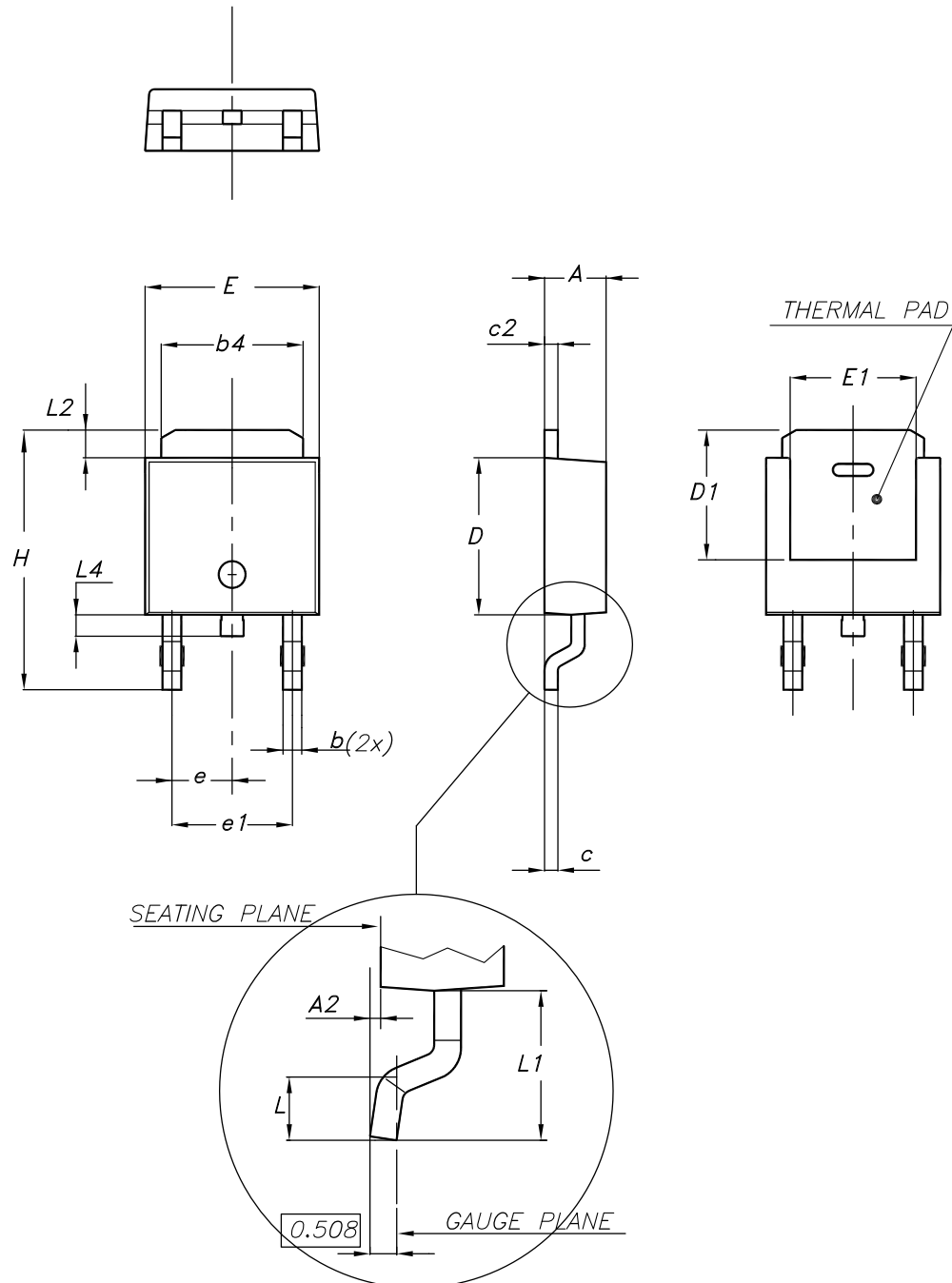
0068772_type-C2_rev36

Table 10. DPAK (TO-252) type C2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.10		5.60
E	6.50	6.60	6.70
E1	5.20		5.50
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

4.4 DPAK (TO-252) type E package information

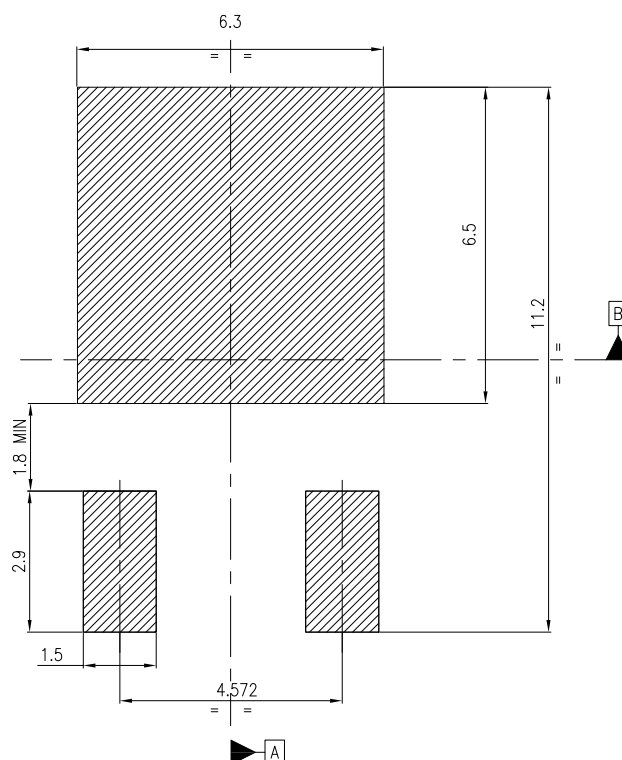
Figure 28. DPAK (TO-252) type E package outline



0068772_typeE_rev.36

Table 11. DPAK (TO-252) type E mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

Figure 29. DPAK (TO-252) recommended footprint (dimensions are in mm)


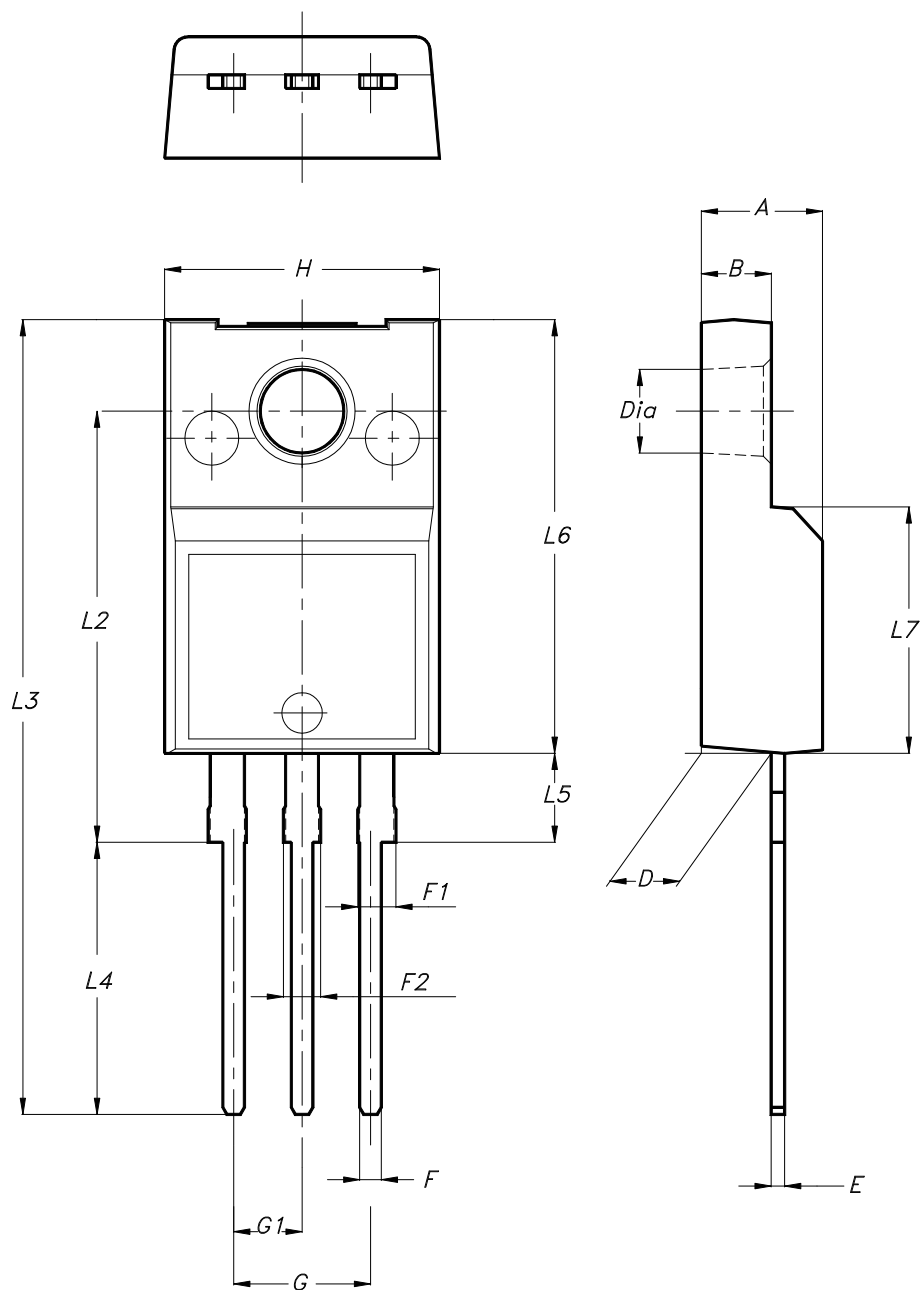
Notes:

- 1) This footprint is able to ensure insulation up to 630 Vrms (according to CEI IEC 664-1)
- 2) The device must be positioned within $\Phi 0.05$ A B

FP_0068772_36

4.5 TO-220FP type B package information

Figure 30. TO-220FP type B package outline



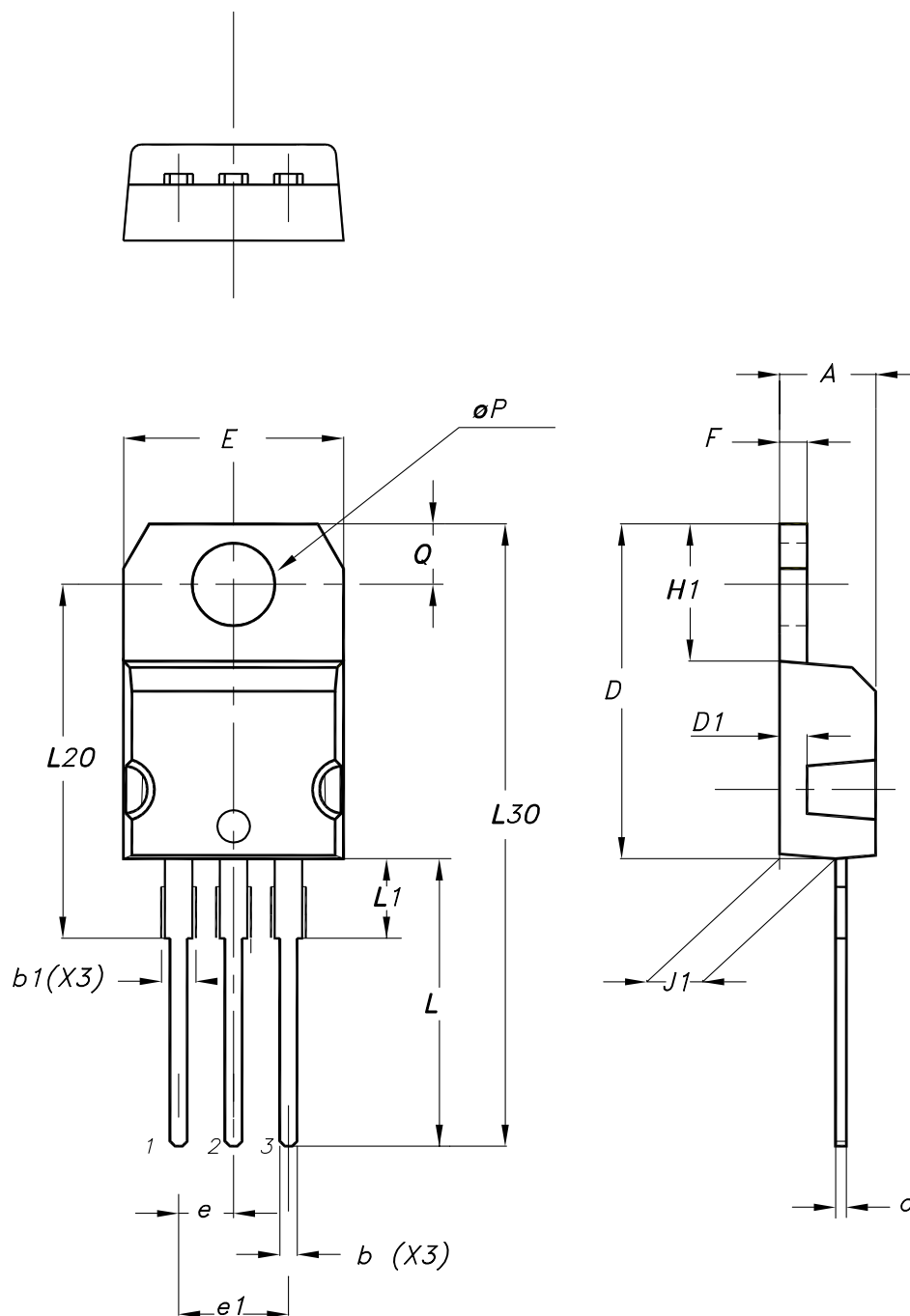
7012510_B_rev.14

Table 12. TO-220FP type B package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

4.6 TO-220 type A package information

Figure 31. TO-220 type A package outline



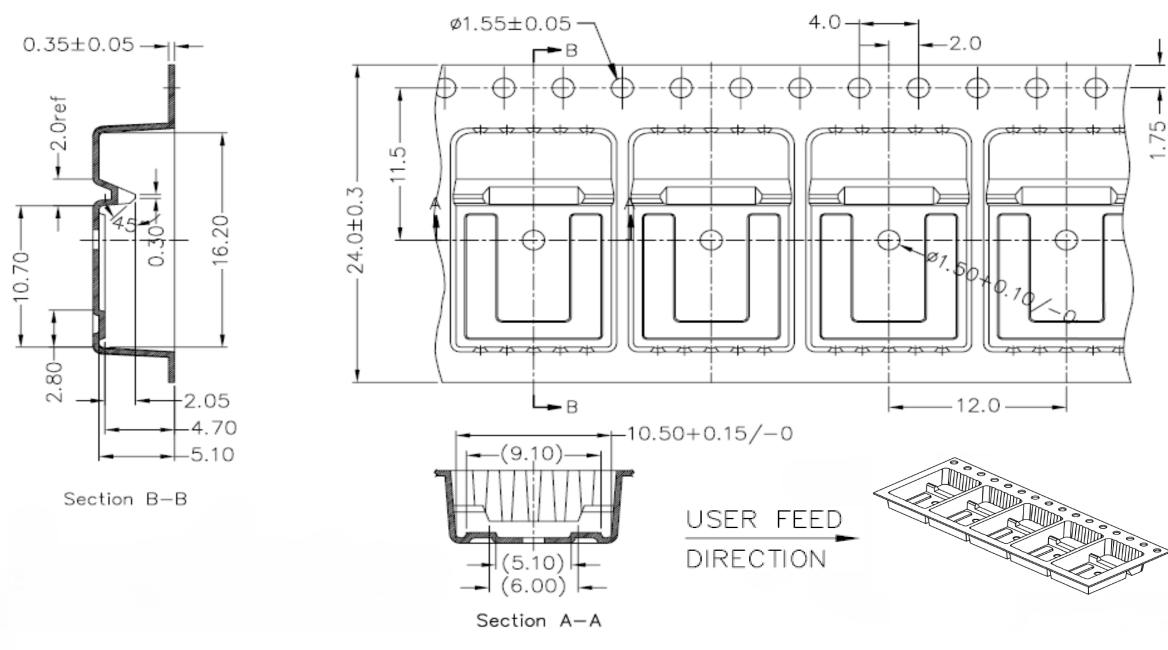
0015988_typeA_Rev_24

Table 13. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

4.7 D²PAK packing information

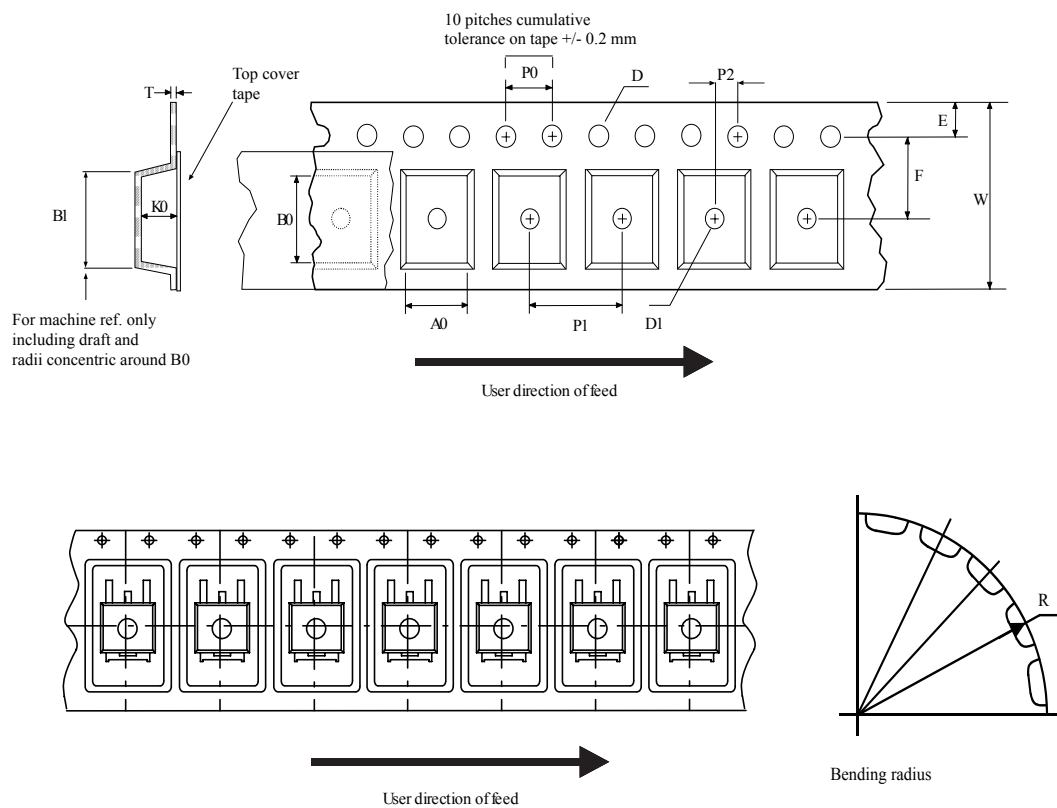
Figure 32. D²PAK tape drawing (dimensions are in mm)



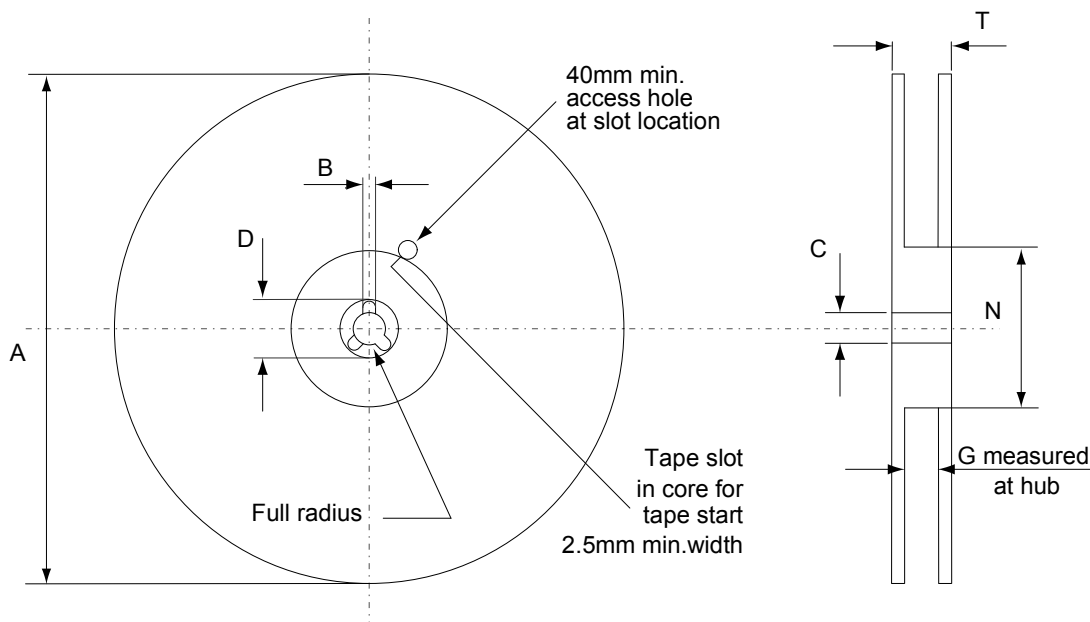
DM01095771 2

4.8 DPAK (TO-252) packing information

Figure 33. DPAK (TO-252) tape outline



AM08852v1

Figure 34. DPAK (TO-252) reel outline


AM06038v1

Table 14. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			



5 Ordering information

Table 15. Order codes

Order codes	Marking	Package	Packing
STB11N65M5	11N65M5	D ² PAK	Tape and reel
STD11N65M5		DPAK	
STF11N65M5		TO-220FP	Tube
STP11N65M5		TO-220	

Revision history

Table 16. Document revision history

Date	Version	Changes
23-Feb-2012	1	First release.
03-Dec-2012	2	– Minor text changes in cover page – Added IPAK packages – Added <i>Section 2.1: Electrical characteristics (curves)</i> – Updated <i>Section 5: Packaging mechanical data</i> – Modified: <i>note 2 on Table 2</i> – Updated: mechanical data for TO-220FP package
02-May-2018	3	The part number STU11N65M5 has been moved to a separate datasheet. Removed maturity status indication from cover page. The document status is production data. Updated title and features in cover page, <i>Section 1 Electrical ratings</i>, <i>Section 2 Electrical characteristics</i>, <i>Section 2.1 Electrical characteristics curves</i> and <i>Section 4 Package information</i>. Minor text changes.
17-Jul-2025	4	Updated Section 4: Package information. Minor text changes.



Contents

1	Electrical ratings	2
2	Electrical characteristics	3
2.1	Electrical characteristics curves	5
3	Test circuits	8
4	Package information	9
4.1	D ² PAK (TO-263) type A package information	9
4.2	DPAK (TO-252) type A package information	12
4.3	DPAK (TO-252) type C2 package information	14
4.4	DPAK (TO-252) type E package information	16
4.5	TO-220FP type B package information	19
4.6	TO-220 type A package information	21
4.7	D ² PAK packing information	23
4.8	DPAK (TO-252) packing information	24
5	Ordering information	26
	Revision history	27



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